



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

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| Title of Invention | METHOD OF FABRICATING A BIPOLAR JUNCTION TRANSISTOR | | |
| Application Type : regular, utility Attorney Docket Number : NAUP0536USA | | | |
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|  as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith. | | | |